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	Filing Date	See Attached Schedule
	First Named Inventor	See Attached Schedule
	Art Unit	See Attached Schedule
	Examiner Name	See Attached Schedule
	Attorney Docket Number	See Attached Schedule

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☐ Applicant/Inventor.

☒ Assignee of record of the entire interest. See 37 CFR 3.71.  
Statement under 37 CFR 3.73(b) is enclosed. (Form PTO/SB/96)

### SIGNATURE OF Applicant or Assignee of Record

Signature		
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NOTE: Signatures of all the inventors or assignees of record of the entire interest or their representative(s) are required. Submit multiple forms if more than one signature is required, see below.

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## Patent Application Schedule

<u>Attorney Docket</u>	<u>Inventor Name</u>	<u>Status</u>	<u>Appln Serial No.</u>	<u>Title of the Invention</u>
2959P	Pakala, Mahendra	Pending Filed on 11/14/2003	10/714,357	STRESS ASSISTED CURRENT DRIVEN SWITCHING FOR MAGNETIC MEMORY APPLICATIONS
3037D	Nguyen, Paul	Pending Filed on 3/13/2007	11/685,723	SPIN TRANSFER MAGNETIC ELEMENT HAVING LOW SATURATION MAGNETIZATION FREE LAYERS
3066C	Nguyen, Paul	Pending Filed on 9/30/2005	11/239,969	SPIN TRANSFER MAGNETIC ELEMENT WITH FREE LAYERS HAVING HIGH PERPENDICULAR ANISOTROPY AND IN-PLAN EQUILIBRIUM MAGNETIZATION
3230C	Diao, Zhitao	Pending Filed on 1/29/2007	11/699,160	MAGNETIC ELEMENTS WITH SPIN ENGINEERED INSERTION LAYERS AND MRAM DEVICES USING THE MAGNETIC ELEMENTS
3352P	Pakala, Mahendra	Pending Filed on 12/5/2005	11/294,766	METHOD AND SYSTEM FOR PROVIDING A HIGHLY TEXTURED MAGNETORESISTANCE ELEMENT AND MAGNETIC MEMORY
3557P	Diao, Zhitao	Pending Filed on 6/8/2005	11/147,944	FAST MAGNETIC MEMORY DEVICES UTILIZING SPIN TRANSFER AND MAGNETIC ELEMENTS USED THEREIN
3615P	Huai, Yiming	Pending Filed on 7/1/2005	11/173,087	MAGNETIC ELEMENTS HAVING A BIAS FIELD AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC ELEMENTS
3628P	Apalkov, Dmytro	Pending Filed on 7/19/2005	11/185,507	MAGNETIC ELEMENTS HAVING IMPROVED SWITCHING CHARACTERISTICS AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC ELEMENTS
3667P	Pakala, Mahendra	Pending Filed on 8/23/2005	11/210,452	SPIN-TRANSFER SWITCHING MAGNETIC ELEMENTS USING FERRIMAGNETS AND MAGNETIC MEMORIES USING THE MAGNETIC ELEMENTS
3671P	Chen, Eugene	Pending Filed on 8/31/2005	11/217,258	CURRENT DRIVEN SWITCHING OF MAGNETIC STORAGE CELLS UTILIZING SPIN TRANSFER AND MAGNETIC MEMORIES USING SUCH CELLS

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3691P	Chen, Eugene	Pending Filed on 8/31/2005	11/217,524	CURRENT DRIVEN SWITCHING OF MAGNETIC STORAGE CELLS UTILIZING SPIN TRANSFER AND MAGNETIC MEMORIES USING SUCH CELLS
3709P	Apalkov, Dmytro	Pending Filed on 10/14/2005	11/251,428	SPIN TRANSFER BASED MAGNETIC STORAGE CELLS UTILIZING GRANULAR FREE LAYERS AND MAGNETIC MEMORIES USING SUCH CELLS
3725P	Chen, Eugene	Pending Filed on 10/27/2005	11/260,778	Current Driven Switched Magnetic Storage Cells Having Improved Read and Write Margins and Magnetic Memories Using Such Cells
3753P	Chen, Eugene	Pending Filed on 2/24/2006	11/361,267	CURRENT DRIVEN MEMORY CELLS HAVING ENHANCED CURRENT AND ENHANCED CURRENT SYMMETRY
3846P	Luo, Xiao	Pending Filed on 5/18/2006	11/436,446	High Density Magnetic Memory Cell Layout for Spin Transfer Torque Magnetic Memories Utilizing Donut Shaped Transistors
3850P	Luo, Xiao	Pending Filed on 6/1/2006	11/446,391	METHOD AND SYSTEM FOR PROVIDING A MAGNETIC MEMORY STRUCTURE UTILIZING SPIN TRANSFER
3856CIP	Ding, Yunfei	Pending Filed on 4/17/2007	11/736,290	METHOD AND SYSTEM FOR USING A PULSED FIELD TO ASSIST SPIN TRANSFER INDUCED SWITCHING OF MAGNETIC MEMORY ELEMENTS
3856P	Ding, Yunfei	Pending Filed on 7/17/2006	11/487,723	METHOD AND SYSTEM FOR USING A PULSED FIELD TO ASSIST SPIN TRANSFER INDUCED SWITCHING OF MAGNETIC MEMORY ELEMENTS
3861P	Chen, Eugene	Pending Filed on 6/26/2006	11/476,171	Current Driven Switching of Magnetic Storage Cells Utilizing Spin Transfer and Magnetic Memories Using Such Cells Having Enhanced Read and Write Margins
3887CIP	Huai, Yiming	Pending Filed on 9/20/2006	11/523,872	MAGNETIC ELEMENT UTILIZING FREE LAYER ENGINEERING
3887P	Huai, Yiming	Pending Filed on 7/14/2006	11/487,552	MAGNETIC ELEMENT UTILIZING FREE LAYER ENGINEERING

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<u>Attorney Docket</u>	<u>Inventor Name</u>	<u>Status</u>	<u>Appln Serial No.</u>	<u>Title of the Invention</u>
3958P	Wang, Lien-Chang	Pending Filed on 10/30/2006	11/589,347	METHOD AND SYSTEM FOR PROVIDING A CONTACT TO A MAGNETIC ELEMENT IN A MEMORY
4025P	Diao, Zhitao	Pending Filed on 3/27/2007	11/692,090	METHOD AND SYSTEM FOR PROVIDING FIELD BIASED MAGNETIC MEMORY DEVICES
4090P	Li, Zhanjie	Pending Filed on 4/3/2007	11/695,614	METHOD AND SYSTEM FOR PROVIDING DOMAIN WALL ASSISTED SWITCHING OF MAGNETIC ELEMENTS AND MAGNETIC MEMORIES USING SUCH MAGNETIC ELEMENTS
2929P	Huai, Yiming	Allowed	10/839,064	MAGNETORESISTIVE ELEMENT HAVING REDUCED SPIN TRANSFER INDUCED NOISE
2990D	Huai, Yiming	Allowed	11/413,744	Magnetic Elements with Ballistic Magnetoresistance Utilizing Spin-Transfer and an MRAM Device Using Such Magnetic Elements
3008C	Nguyen, Paul	Allowed	11/256,387	Magnetic Element Utilizing Spin-Transfer and Half-Metals and an MRAM Device Using the Magnetic Element
3037P	Nguyen, Paul	Allowed	10/783,416	SPIN TRANSFER MAGNETIC ELEMENT HAVING LOW SATURATION MAGNETIZATION FREE LAYERS
3095P	Huai, Yiming	Allowed	10/829,313	SPIN TRANSFER MAGNETIC ELEMENTS WITH SPIN DEPOLARIZATION LAYERS
3230P	Diao, Zhitao	Allowed	10/938,219	MAGNETIC ELEMENTS WITH SPIN ENGINEERED INSERTION LAYERS AND MRAM DEVICES USING THE MAGNETIC ELEMENTS
3399P	Huai, Yiming	Allowed	11/027,397	MTJ ELEMENTS WITH HIGH SPIN POLARIZATION LAYERS CONFIGURED FOR SPIN-TRANSFER SWITCHING AND SPINTRONICS DEVICES USING THE MAGNETIC ELEMENTS
3648P	Wang, Lien-Chang	Allowed	11/192,811	MAGNETIC DEVICES HAVING A HARD BIAS FIELD AND MAGNETIC MEMORY DEVICES USING THE MAGNETIC DEVICES